

MoS₂/GO composites for hole injection layer in organic light emitting diodes

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Two-Dimensional MoS₂ and graphene oxide (GO) can be used in organic light emitting diode (OLED) as hole injection layer (HIL) after work function modification. MoS₂ was made by using BuLi intercalation method. Also GO was synthesized using a modified Hummers method. In this work, nanocomposite of MoS₂ and GO were employed as a hole-injection layer to improve the efficiency and air stability of OLED. The OLED with nanocomposite layer show a degraded performance with a luminance power efficiency (LPE), which is lower than that of OLED with poly(3,4-ethylenedioxythiophene): poly(styrene sulfonate) (PEDOT:PSS) layer.

Figure 1 shows the characteristics of OLEDs containing MoS₂-GO composite HILs. The turn-on voltage at 10 cd/m² decreased from 4.3 to 4.24 V as the GO content in the MoS₂-GO composite increased to 40 wt%. Accordingly, the maximum power efficiency increased from 3.12 to 3.77 lm W⁻¹ (from MoS₂-GO 10:0 to 6:4). However, turn-on voltage increased to 4.29 V as the GO content increased to 80 wt%. As a result, maximum power efficiency decreased to 3.2 lm W⁻¹ for MoS₂-GO 2:8. These results revealed that OLEDs with HILs fabricated using MoS₂-GO composites with similar contents of MoS₂ and GO provide the best performances. In the case of the GO HIL, the OLED showed the lowest turn-on voltage of 4.15 V and the highest power efficiency of 4.94 lm W⁻¹. The work functions of MoS₂

and GO are reported to be 4.6 and 4.8 eV, respectively. Therefore, the OLED with GO HIL showed the best performance due to the lowest roughness and high work function of GO.

The properties of nanocomposite layer were examined using atomic force microscopy, field-emission scanning electron microscopy, x-ray photoelectron spectroscopy and ultraviolet photoelectron spectroscopy. Based on these characterization data, the origin of improved device performances was investigated.

Acknowledgement

This research was supported in part by a National Research Foundation of Korea (NRF) grant funded by the Korean government (MSIP) (No. 2014R1A2A1A11051098, 2015K1A3A1A59073839).

Figures

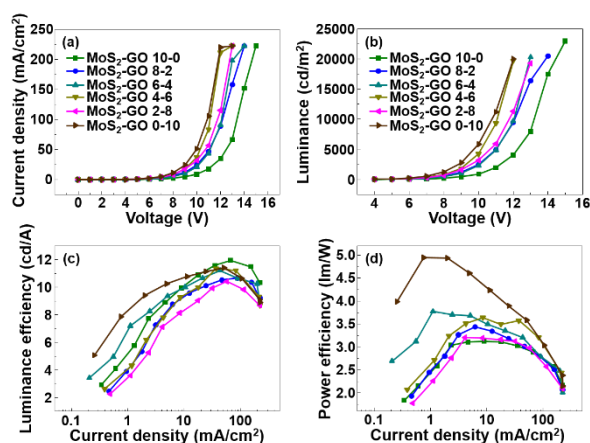


Figure 1: (a) Current-density-voltage, (b) luminance-voltage, (c) luminance-efficiency-current-density, and (d) power-efficiency-current-density characteristics of organic light-emitting diode devices with MoS₂-GO composite as hole injection layer.